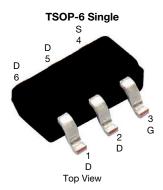




N-Channel 100 V (D-S) MOSFET

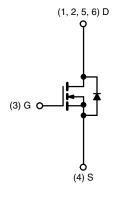


PRODUCT SUMMARY							
V _{DS} (V)	100						
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.170						
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 6 \text{ V}$	0.185						
Q _g typ. (nC)	5.5						
I _D (A)	2.4						
Configuration	Single						

FEATURES

- High-efficiency PWM optimized
- 100 % R_g tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





N-Channel MOSFET

ORDERING INFORMATION				
Package	TSOP-6			
Lead (Pb)-free	Si3430DV-T1-E3			
Lead (Pb)-free and halogen-free	Si3430DV-T1-GE3			

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	5 s	STEADY STATE	UNIT	
Drain-source voltage	V _{DS}	100	100	V		
Gate-source voltage	V_{GS}	± 20	± 20			
Continuous drain current (T _J = 175 °C) ^a	T _A = 25 °C	I _D	2.4	1.8	А	
	T _A = 85 °C		1.7	1.3		
Pulsed drain current		I _{DM}	8	8	A	
Avalanche current	L = 0.1 mH	I _{AR}	6	6		
Repetitive avalanche energy (duty cycle ≤ 1 %)	L = 0.1 IIII	E _{AR}	1.8	1.8	mJ	
Continuous source current (diode conduction) ^a		I _S	1.7	1	Α	
Maximum power dissipation ^a	T _A = 25 °C	В	2	1.14	W	
iviaximum power dissipation "	T _A = 85 °C	P _D	1	0.59	VV	
Operating junction and storage temperature range)	T _J , T _{stq}	-55 to +150	-55 to +150	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient ^a	t ≤ 5 s	R_{thJA}	45	62.5	°C/W	
	Steady state		90	110		
Maximum junction-to-foot (drain)	Steady state	Rt _{hJF}	25	30		

Note

a. Surface mounted on 1" x 1" FR4 board



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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	MBOL TEST CONDITIONS		TYP.	MAX.	UNIT	
Static							
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{DS}, I_D = 250 \mu A$	2	-	4.2	٧	
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zero gate voltage drain current	1	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μΑ	
Zero gate voltage drain current	I _{DSS}	V_{DS} = 80 V, V_{GS} = 0 V, T_J = 85 °C	-	-	25		
On-state drain current a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	8	-	-	Α	
Drain-source on-state resistance a	В	$V_{GS} = 10 \text{ V}, I_D = 2.4 \text{ A}$	-	0.148	0.170	Ω	
Drain-source on-state resistance "	R _{DS(on)}	$V_{GS} = 6 \text{ V}, I_D = 2.3 \text{ A}$	-	0.160	0.185		
Forward transconductance a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 2.4 \text{ A}$	-	7	-	S	
Diode forward voltage a	V_{SD}	I _S = 1.7 A, V _{GS} = 0 V	-	0.8	1.2	V	
Dynamic ^b	Dynamic ^b						
Total gate charge	Q_g		-	5.5	8.2		
Gate-source charge	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2.4 \text{ A}$	-	1.5	-	nC	
Gate-drain charge	Q_{gd}		-	1.4	-	1	
Gate resistance	R_g		1	-	4	Ω	
Turn-on delay time	t _{d(on)}		-	9	20		
Rise time	t _r	$V_{DD} = 50 \text{ V}, R_{L} = 50 \Omega$	-	11	20	ns	
Turn-off delay time	t _{d(off)}	$I_D \cong 1$ A, $V_{GEN} = 10$ V, $R_g = 6$ Ω	-	16	30	115	
Fall time	t _f		-	9	20		
Gate resistance	R_g	V _{GS} = 0.1 V, f = 5 MHz	-	2.8	-	Ω	
Source-drain reverse recovery time	t _{rr}	I _F = 1.7 A, di/dt = 100 A/μs	-	50	80	ns	

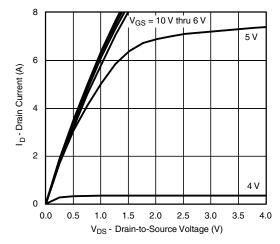
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

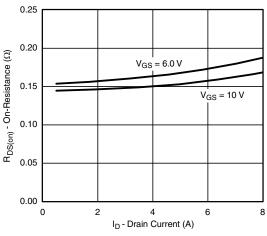
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



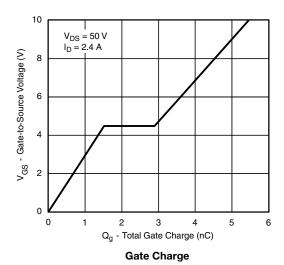
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

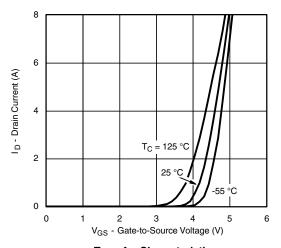


Output Characteristics

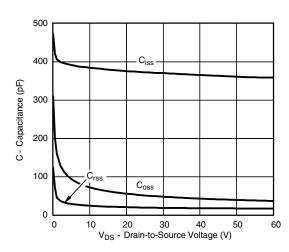


On-Resistance vs. Drain Current

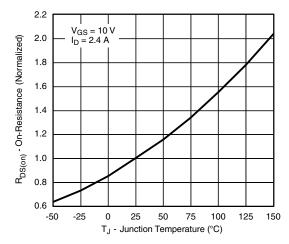




Transfer Characteristics



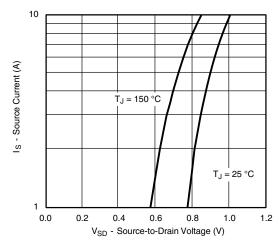
Capacitance



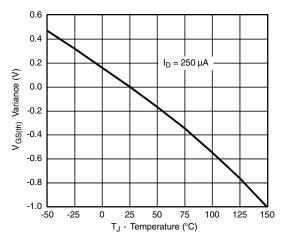
On-Resistance vs. Junction Temperature



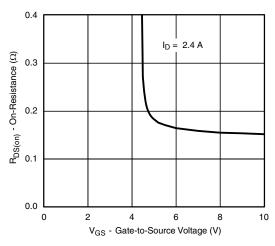
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



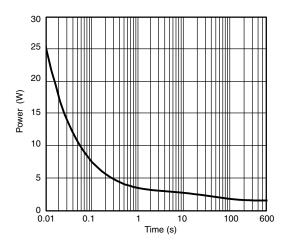
Source-Drain Diode Forward Voltage



Threshold Voltage



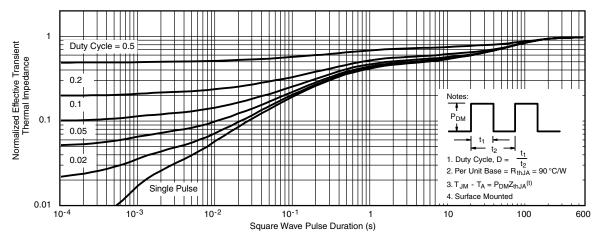
On-Resistance vs. Gate-to-Source Voltage



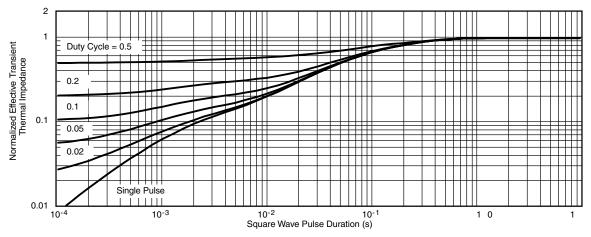
Single Pulse Power



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

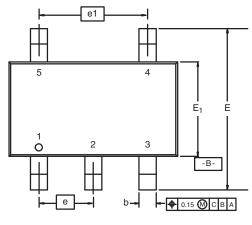
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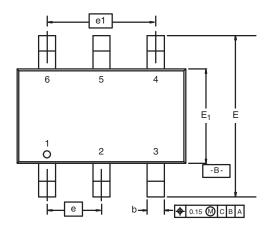




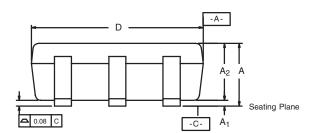
TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C

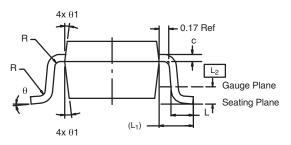




5-LEAD TSOP





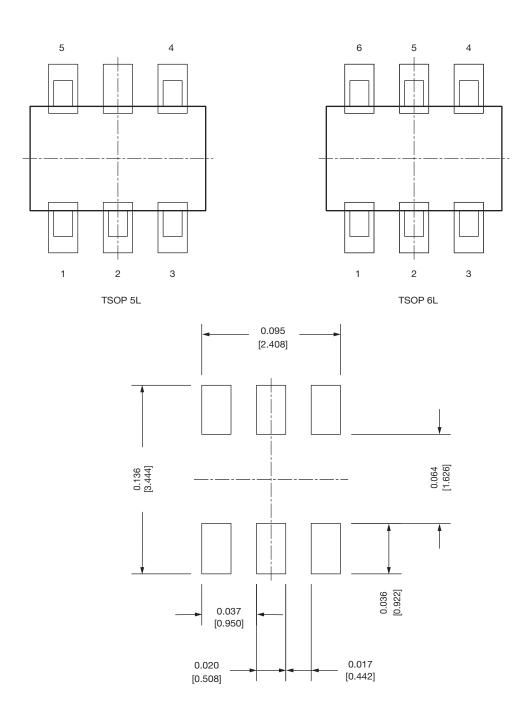


	MIL	LIMETER	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁	0.60 Ref				0.024 Ref		
L ₂	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1	7° Nom 7° Nom						
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Document Number: 71200 18-Dec-06



Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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